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PATENT ABSTRACTS OF JAPAN

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## (54) MANUFACTURE OF SEMICONDUCTOR SUPERLATTICE

(57) Abstract:

put a hetero-epitaxial growth method, in which excellent crystal quality and an Si layer or a Ge-Si layer and an Si layer on an Si substrate, and also to PURPOSE: To form a Ge layer and high growth speed can be obtained, into practical use.

CONSTITUTION: The title semiconductor superlattice

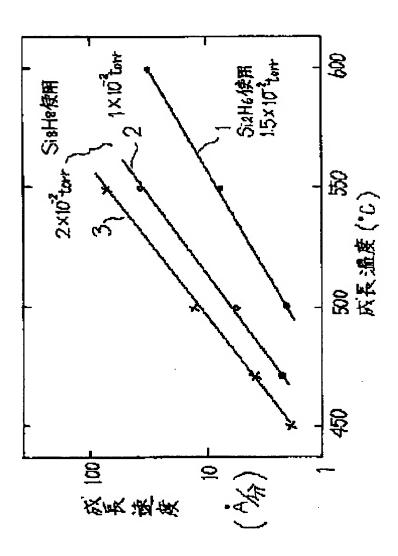
manufacturing method is the method with which a Ge layer and an Si layer or Ge-Si layer and an Si layer are epitaxially grown on an Si substrate by conducting a depressed CVD method under the atmosphere containing oxidizing impurity gas of 1000ppb or lower using GeH4 and trisilane (Si3H8) as raw gas and also using H2 or inert gas as carrier gas.

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